



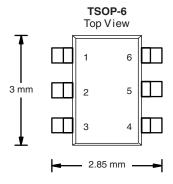
P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A)		
- 20	0.042 at V _{GS} = - 4.5 V	- 5.6		
	0.057 at V _{GS} = - 2.5 V	- 4.8		
	0.080 at V _{GS} = - 1.8 V	- 4.1		

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs: 1.8 V Rated
- Compliant to RoHS Directive 2002/95/EC

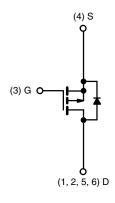




Ordering Information: Si3433BDV-T1-E3 (Lead (Pb)-free)

Si3433BDV-T1-GE3 (Lead (Pb)-free and Halogen-free)

Marking Code: B3xxx



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 8		V
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	- I _D	- 5.6	- 4.3	
	T _A = 85 °C		- 4.1	- 3.1	
Pulsed Drain Current		I _{DM}	- 20		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.7	- 0.9	
Maximum Power Dissipation ^a	T _A = 25 °C	В	2.0	1.1	14/
	T _A = 85 °C	P _D	1.0	0.6	W
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian de Analian to	t ≤ 5 s	- R _{thJA}	50	60	
Maximum Junction-to-Ambient ^a	Steady State		90	110	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	35	42	

Notes

a. Surface Mounted on 1" x 1" FR4 board.

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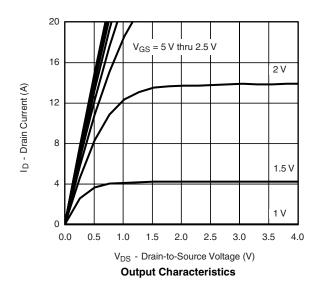
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.45		- 0.85	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V		- 1			
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			- 5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 5.6 A		0.034	0.042		
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 4.8 A		0.045	0.057	Ω	
		V _{GS} = - 1.8 V, I _D = - 1 A		0.060	0.080		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 5.6 A		10		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.7 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			12	18		
Gate-Source Charge	Q _{gs}	Q_{gs} $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -5.6 \text{ A}$		1.7		nC	
Gate-Drain Charge	Q _{gd}			3.5			
Turn-On Delay Time	t _{d(on)}			15	25		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		45	75		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, $V_{GEN}=$ - 4.5 V, $R_g=$ 6 Ω		80	130	ns	
Fall Time	t _f			60	100		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.7 A, dl/dt = 100 A/μs		40	70		

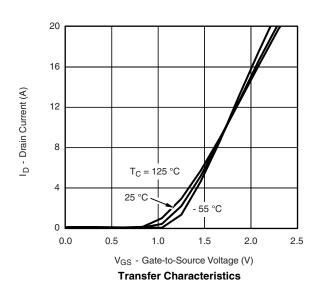
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



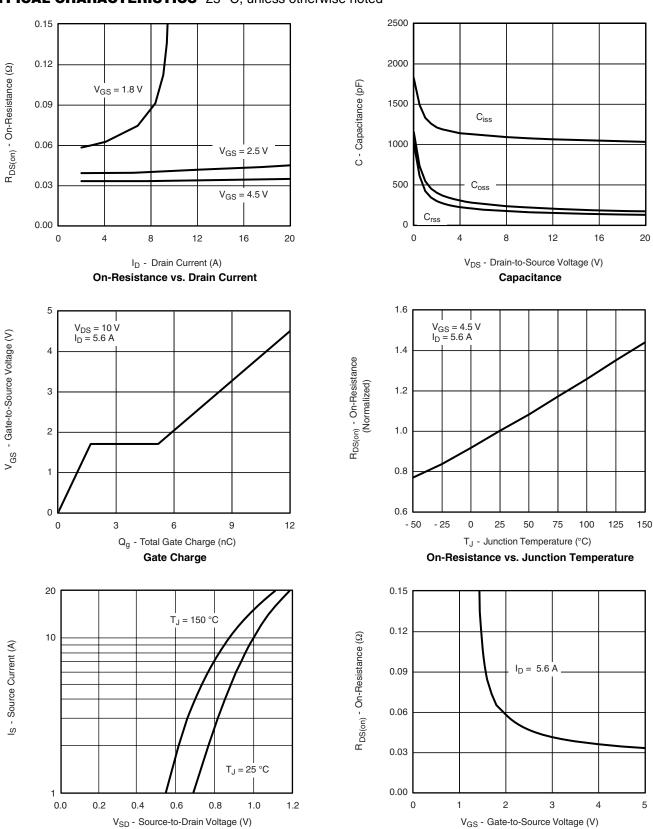








TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



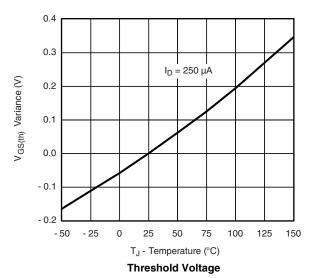
Source-Drain Diode Forward Voltage

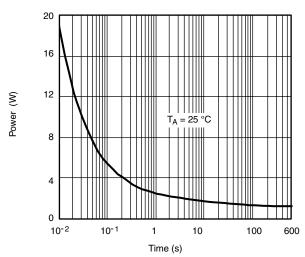
On-Resistance vs. Gate-to-Source Voltage

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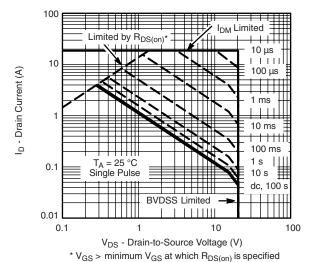
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

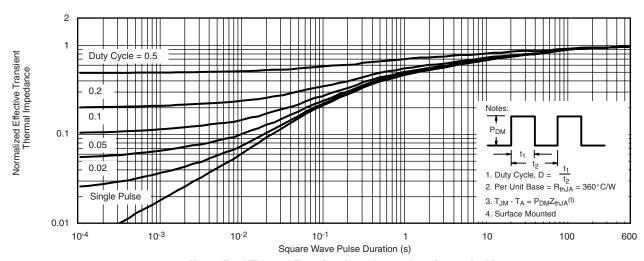




Single Pulse Power



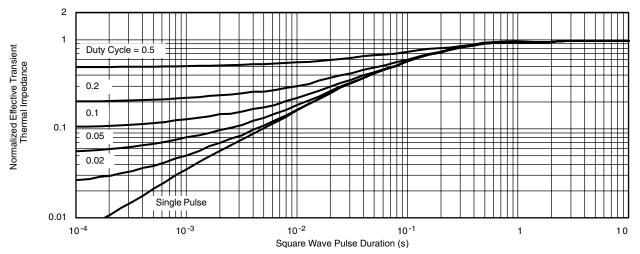
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72027.



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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

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